

Generic LibreSilicon process HKUST (NFF)

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Abstract

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This is the specification of the free silicon manufacturing standard for manufacturing the ls180nm¹ standard logic cells and related free technology nodes from the LibreSilicon project.

For further clarification consult the complete documentation of the process.

¹<https://github.com/leviathanch/ls180nm>

Process Flow of Lanceville Technologies LibreSilicon 180nm

- Project: LibreSilicon 180nm
- Name: Lanceville Technologies Group
- Substrate: P-Substrate silicon wafer <100>
- Date: February 12, 2018



Step Number	Process	Requirements
0.1	Initial Clean	H2SO4 + H2O2, 10mins, 120C
0.2	HF dip	1 min
0.3	Dry the wafer automatically	
0.4	Silicon dioxide growth	1000nm